

TOSHIBA**2SC5096FT**

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC5096FT

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

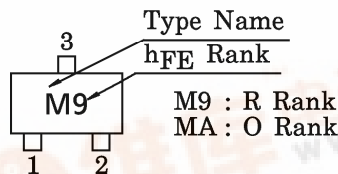
Unit in mm

- Low Noise Figure, High Gain.
- NF=1.8dB, $|S_{21e}|^2=7.5\text{dB}$ ($f=2\text{GHz}$)

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	8	V
Emitter-Base Voltage	V_{EBO}	1.5	V
Base Current	I_B	7	mA
Collector Current	I_C	15	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~125	$^\circ\text{C}$

MARKING



		1. BASE 2. EMITTER 3. COLLECTOR
JEDEC	—	
EIAJ	—	
TOSHIBA	2-1B1A	

MICROWAVE CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	f_T	$V_{CE}=6\text{V}, I_C=7\text{mA}$	7	10	—	GHz
Insertion Gain	$ S_{21e} ^2 (1)$	$V_{CE}=6\text{V}, I_C=7\text{mA}, f=1\text{GHz}$	—	13	—	dB
	$ S_{21e} ^2 (2)$	$V_{CE}=6\text{V}, I_C=7\text{mA}, f=2\text{GHz}$	4.5	7.5	—	
Noise Figure	NF (1)	$V_{CE}=6\text{V}, I_C=3\text{mA}, f=1\text{GHz}$	—	1.4	—	dB
	NF (2)	$V_{CE}=6\text{V}, I_C=3\text{mA}, f=2\text{GHz}$	—	1.8	3.0	

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=10\text{V}, I_E=0$	—	—	1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=1\text{V}, I_C=0$	—	—	1	μA
DC Current Gain	h_{FE} (Note 1)	$V_{CE}=6\text{V}, I_C=7\text{mA}$	50	—	160	—
Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$	—	0.5	—	pF
Reverse Transfer Capacitance	C_{re}	(Note 2)	—	0.4	0.85	pF

(Note 1) : h_{FE} Classification R : 50~100, O : 80~160(Note 2) : C_{re} is measured by 3 terminal method with capacitance bridge.

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